

Serial No. 09/735,005

Docket No. NEC 444

Amendment I under Rule 116**AMENDMENTS TO THE CLAIMS:**

Kindly cancel claims 37 - 40, 45, and 47-48, without prejudice.

This listing of claims will replace all prior versions and listings of claims in the Application:

Claims 1 - 41 (canceled)

Claim 42 (previously presented): A method of manufacturing a semiconductor device, comprising:

performing a selective etching on a semiconductor substrate having first and second active areas and an isolation area intervening between said first and second active areas, thereby forming a grid-shaped trench in said isolation area of said semiconductor substrate to define a plurality of dummy regions each surrounded by said grid-shaped trench;

forming an insulating layer in said grid-shaped trench;

forming a conductive layer on said semiconductor substrate; and

selectively removing said conductive layer to form a transistor gate over each of said first and second active areas and a dummy gate over each of said dummy regions, said dummy gate having a reduced shape area as compared to a shape area of a corresponding one of said dummy regions.

Claim 43 (previously presented): The method as set forth in claim 42, wherein said insulating layer is formed by chemical mechanical polishing process.

Claim 44 (previously presented): The method as set forth in claim 42, wherein said transistor gate and said dummy gate are formed by use of such a mask pattern that is derived by combining a transistor gate pattern and a dummy gate pattern which is obtained by reducing a mask pattern for forming said grid-shaped trench.

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Claims 45 - 48 (cancelled)

HAYES SOLOWAY P.C.
3450 E. SUNRISE DRIVE,
SUITE 140
TUCSON, AZ 85718
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567